# TVS Diode

Transient Voltage Suppressor Diodes

# ESD5V3U2U Series

Uni-directional Ultra Low ESD / Transient Protection Diode

ESD5V3U2U-03F
ESD5V3U2U-03LRH

## Data Sheet

Revision 1.3, 2013-08-16
Final

Power Management & Multimarket

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| Revision History: Rev. 1.2, 2013-08-16 | |
|---|---|
| **Page or Item** | **Subjects (major changes since previous revision)** |
| **Revision 1.3, 2013-08-16** | |
| 4 + 16 | All marking infos for TSLP-3-7 updated |
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Last Trademarks Update 2010-10-26

# 1 Uni-directional Ultra Low ESD / Transient Protection Diode

## 1.1 Features

- ESD / Transient protection of High-Speed data lines exceeding
  - **IEC61000-4-2 (ESD): ± 20 kV (air / contact)**
  - **IEC61000-4-4 (EFT): ±50 A (5/50 ns)**
  - **IEC61000-4-5 (surge): ±3 A (8/20 µs)**
- Maximum working voltage: $V_{RWM}$ **5.3 V**
- Extremely low capacitance: down to 0.4 pF
- Very low reverse current: $I_R$ < 1 nA typical
- Pb-free package (RoHS compliant) and halogen free package

## 1.2 Application Examples

- ESD / Transient protection of High Speed Interfaces:
  - HDMI, USB 2.0/USB 3.0, DisplayPort, DVI
  - Mobile HDMI Link, MDDI, MIPI.
  - 10/100/1000 Ethernet, Firewire, S-ATA, etc.

## 1.3 Product Description

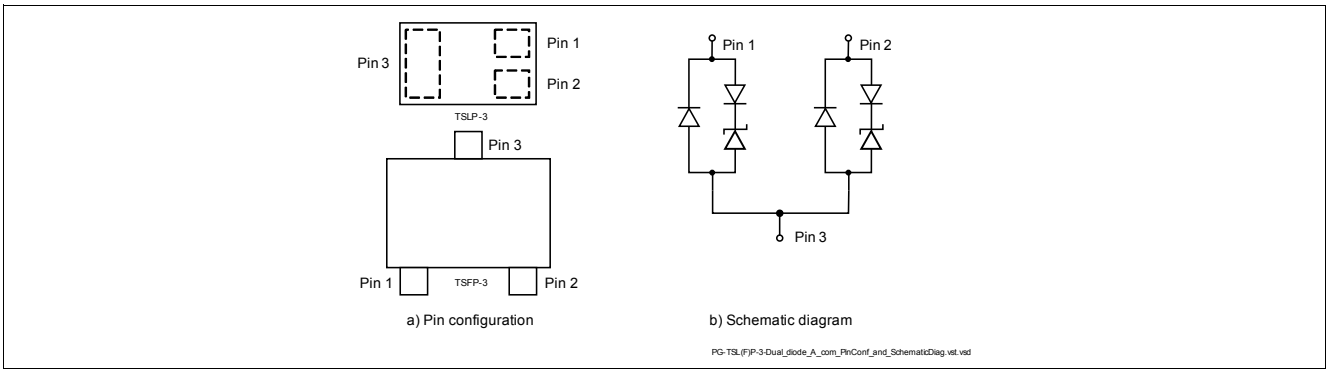



**Figure 1-1 Pin Configuration (a) and Schematic Diagram (b)**

**Table 1-1 Ordering information**

| Type | Package | Configuration | Marking code |
|---|---|---|---|
| ESD5V3U2U-03F | PG-TSFP-3-1 | 2 lines, uni-directional[1)] | Z1 |
| ESD5V3U2U-03LRH | PG-TSLP-3-7 | 2 lines, uni-directional[1)] | Z1 |

1) Or 1 line, bi-directional between pins 1 and 2, if pin 3 is not connected

# 2 Characteristics

**Table 2-1 Maximum Rating at $T_A$ = 25 °C, unless otherwise specified**

| Parameter | Symbol | Values | | | Unit |
|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | |
| ESD (air / contact) discharge[1)] | $V_{ESD}$ | -20 | – | 20 | kV |
| Peak pulse current ($t_p$ = 8/20 µs)[2)] | $I_{PP}$ | -3 | – | 3 | A |
| Operating temperature range | $T_{OP}$ | -40 | – | 125 | °C |
| Storage temperage | $T_{stg}$ | -65 | – | 150 | °C |

1) $V_{ESD}$ according to IEC61000-4-2

2) $I_{PP}$ according to IEC61000-4-5

***Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.***

## 2.1 Electrical Characteristics at $T_A$ = 25 °C, unless otherwise specified

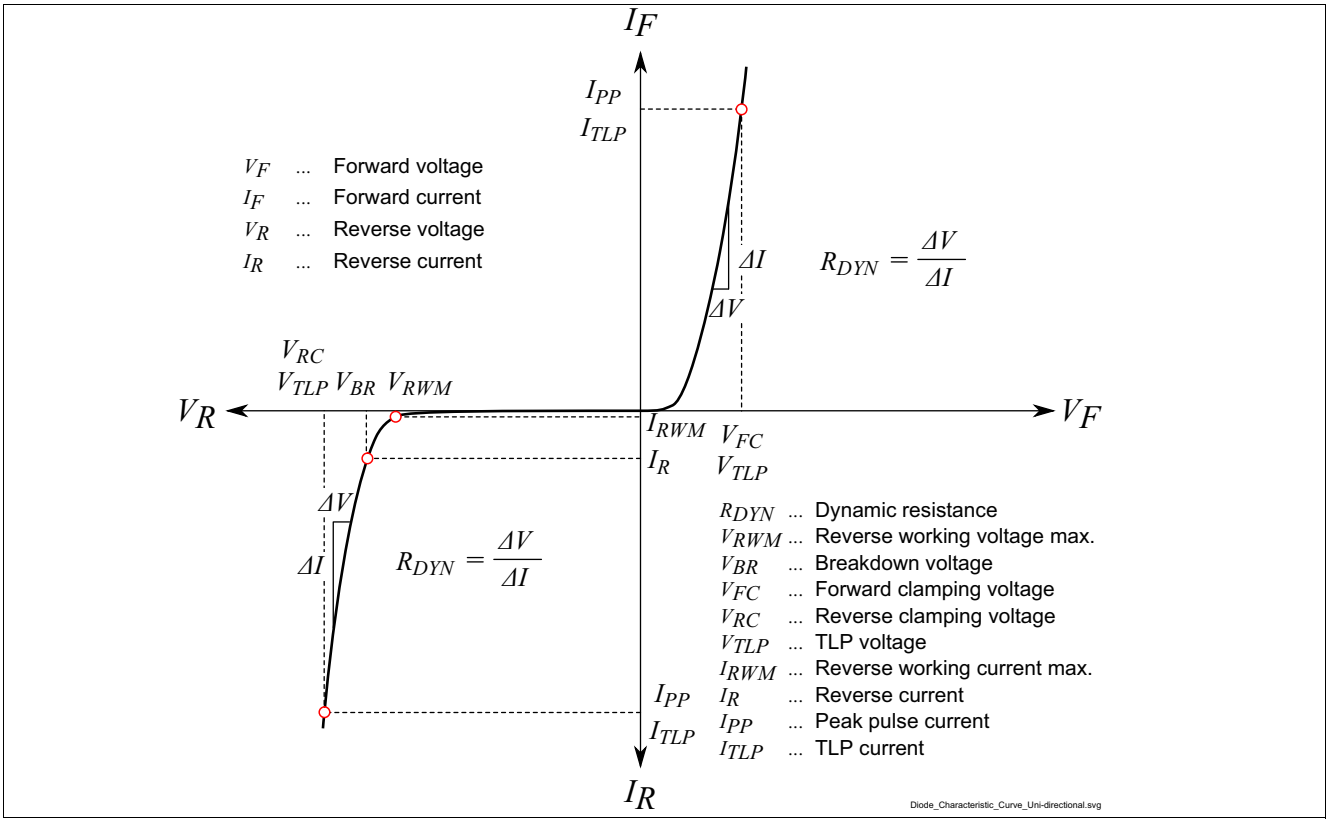



**Figure 2-1 Definitions of electrical characteristics**

**Table 2-2 DC characteristics at $T_A$ = 25 °C, unless otherwise specified**

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Reverse working voltage | $V_{RWM}$ | – | – | 5.3 | V | |
| Breakdown voltage | $V_{BR}$ | 6 | – | – | V | $I_{BR}$ = 1 mA, from Pin 1/2 to Pin 3 |
| Reverse current | $I_R$ | – | <1 | 50 | nA | $V_R$ = 5.3 V, from Pin 1/2 to Pin 3 |

**Table 2-3 RF characteristics at $T_A$ = 25 °C, unless otherwise specified**

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Line capacitance[1)] | $C_L$ | – | 0.4 | 0.6 | pF | $V_R$ = 0 V, $f$ = 1 MHz from pin 1/2 to pin 3 |
| | | – | 0.2 | 0.4 | pF | $V_R$ = 0 V, $f$ = 1 MHz from pin 1 to 2, pin 3[1)] not connected |

1) Total capacitance line to ground

**Table 2-4 ESD Characteristics** at $T_A$ = 25 °C, unless otherwise specified

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Clamping voltage[1)] | $V_{CL}$ | – | 19 | – | V | $I_{TLP}$ = 16 A, from Pin 1/2 to Pin 3 |
| | | – | 28 | – | V | $I_{TLP}$ = 30 A, from Pin 1/2 to Pin 3 |
| Forward clamping voltage[1)] | $V_{FC}$ | – | 10 | – | V | $I_{TLP}$ = 16 A, from Pin 3 to Pin 1/2 |
| | | – | 17 | – | V | $I_{TLP}$ = 30 A, from Pin 3 to Pin 1/2 |
| Dynamic resistance[1)] | $R_{DYN}$ | – | 0.6 | – | V | Pin 1/2 to Pin 3 |
| | | – | 0.4 | – | V | Pin 3 to Pin 1/2 |

1)Please refer to Application Note AN210[1]. TLP parameter: $Z_0$ = 50 Ω , $t_p$ = 100ns, $t_r$ = 300ps, averaging window: $t_1$ = 30 ns to $t_2$ = 60 ns, extraction of dynamic resistance using least squares fit of TLP charactertistics between $I_{PP1}$ = 10 A and $I_{PP2}$ = 40 A.

**Table 2-5 Surge characteristics at $T_A$ = 25 °C, unless otherwise specified**

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---|---|---|---|---|---|
| | | Min. | Typ. | Max. | | |
| Clamping voltage | $V_{CL}$ | – | 10 | 13 | V | $I_{PP}$ = 1 A, $t_p$=8/20 µs[1] from Pin 1/2 to Pin 3 |
| | | – | 12 | 15 | V | $I_{PP}$ = 3A, $t_p$ =8/20 µs[1] from Pin 1/2 to Pin 3 |
| Forward clamping voltage | $V_{FC}$ | – | 2 | 4 | V | $I_{PP}$ = 1 A, $t_p$ =8/20 µs[1] from Pin 3 to Pin 1/2 |
| | | – | 4 | 6 | V | $I_{PP}$ = 3A, $t_p$ =8/20 µs[1] from Pin 3to Pin 1/2 |

1) $I_{PP}$ according to IEC61000-4-5

# 3 Typical characteristics

Typical characteristics at  = 25 °C, unless otherwise specified

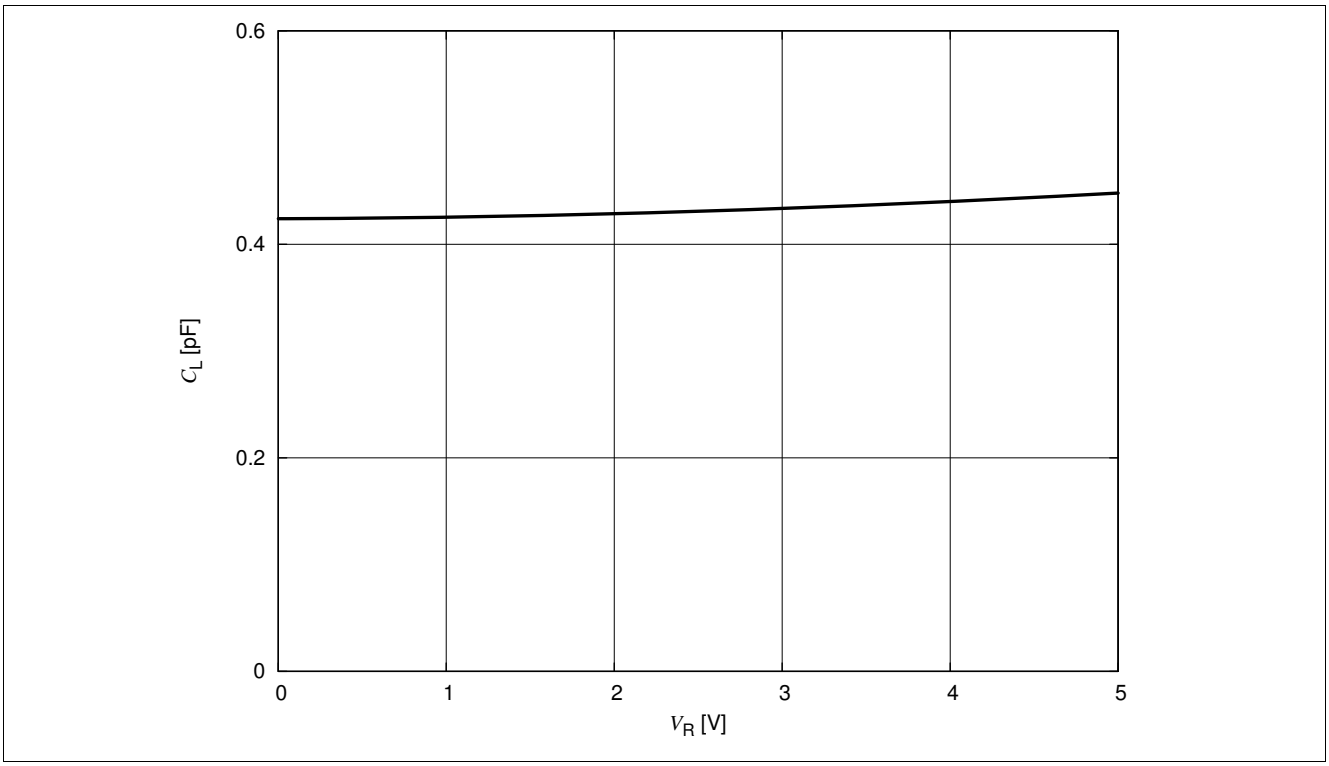



**Figure 3-1 Line capacitance $C_L$=$f(V_R)$, from pin 1/2 to 3, $f$ = 1 MHz**

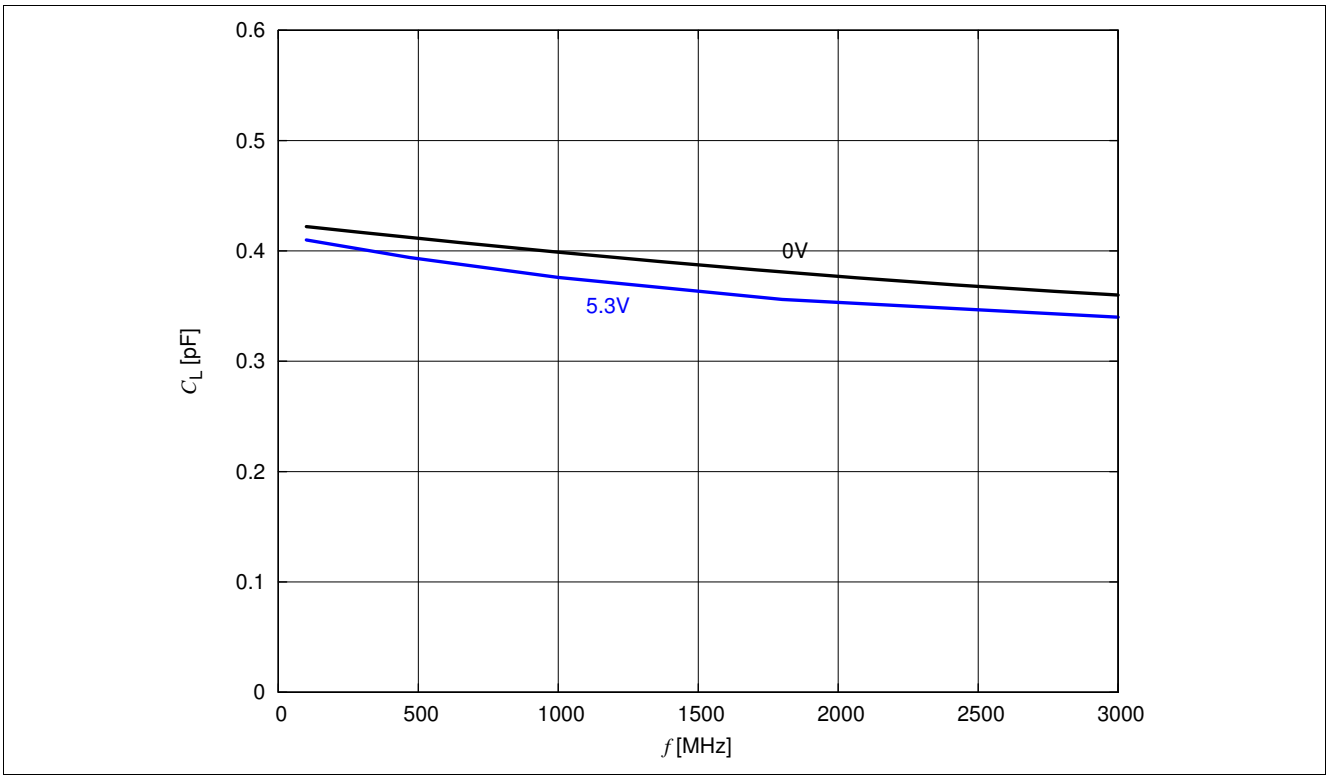



**Figure 3-2 Line capacitance $C_L$=$f(f)$, from pin 1/2 to 3**

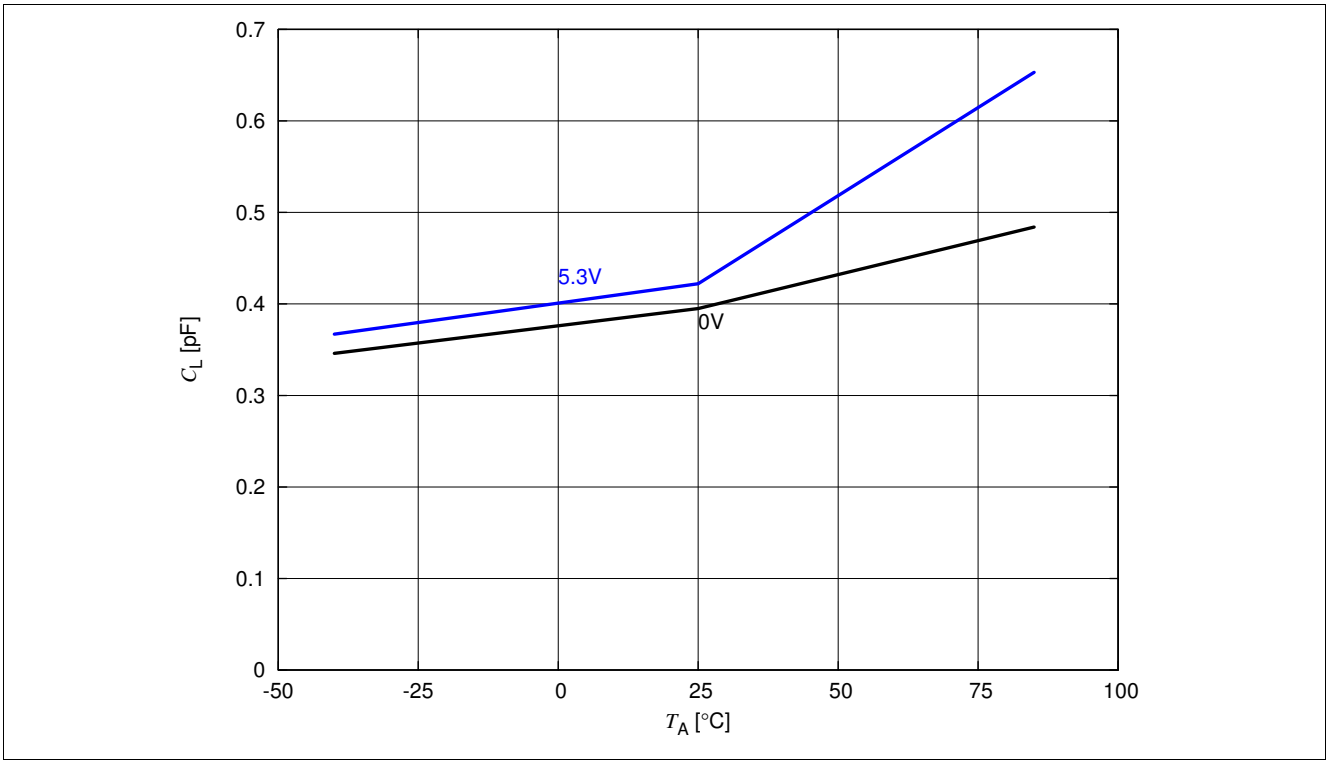



**Figure 3-3 Line capacitance $C_L=f(T_A)$**

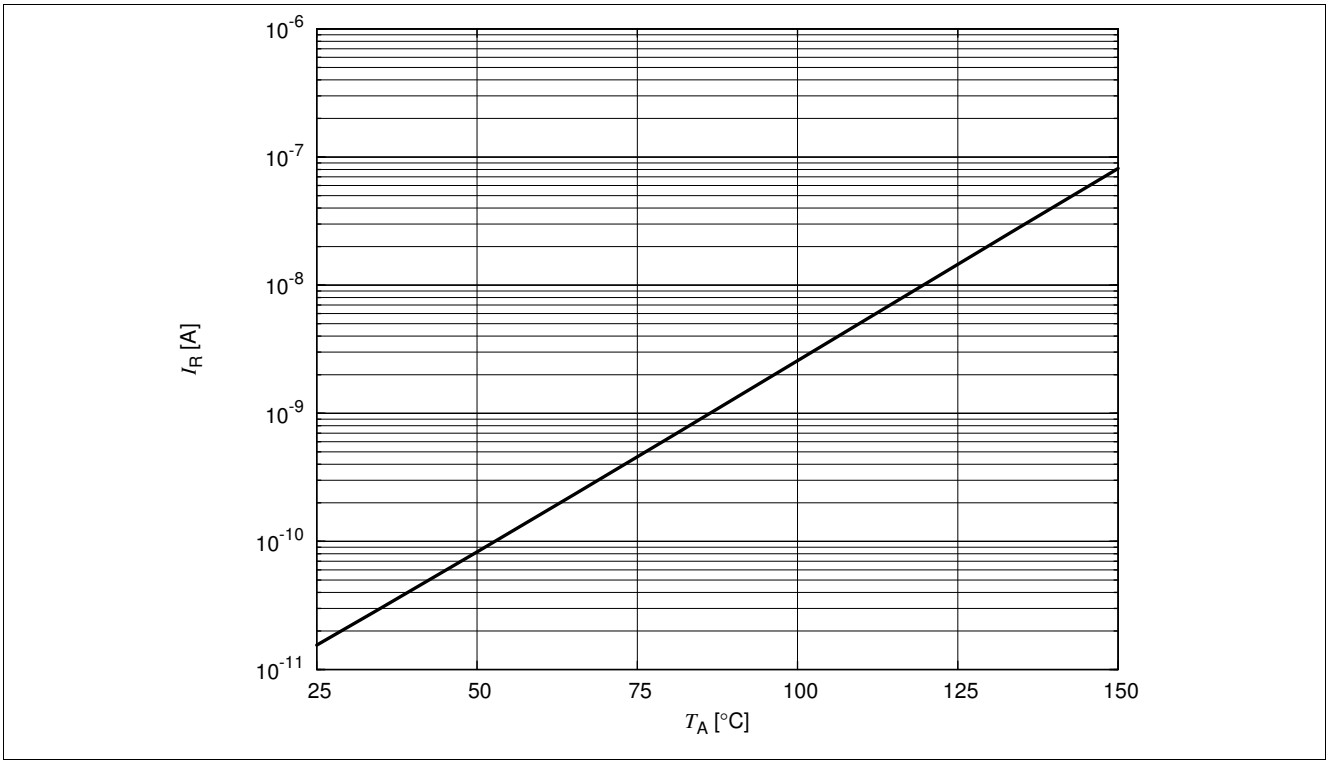



**Figure 3-4 Reverse current $I_R=f(T_A)$ , $V_R$=5.3 $V$, from pin 1/2 to pin 3**

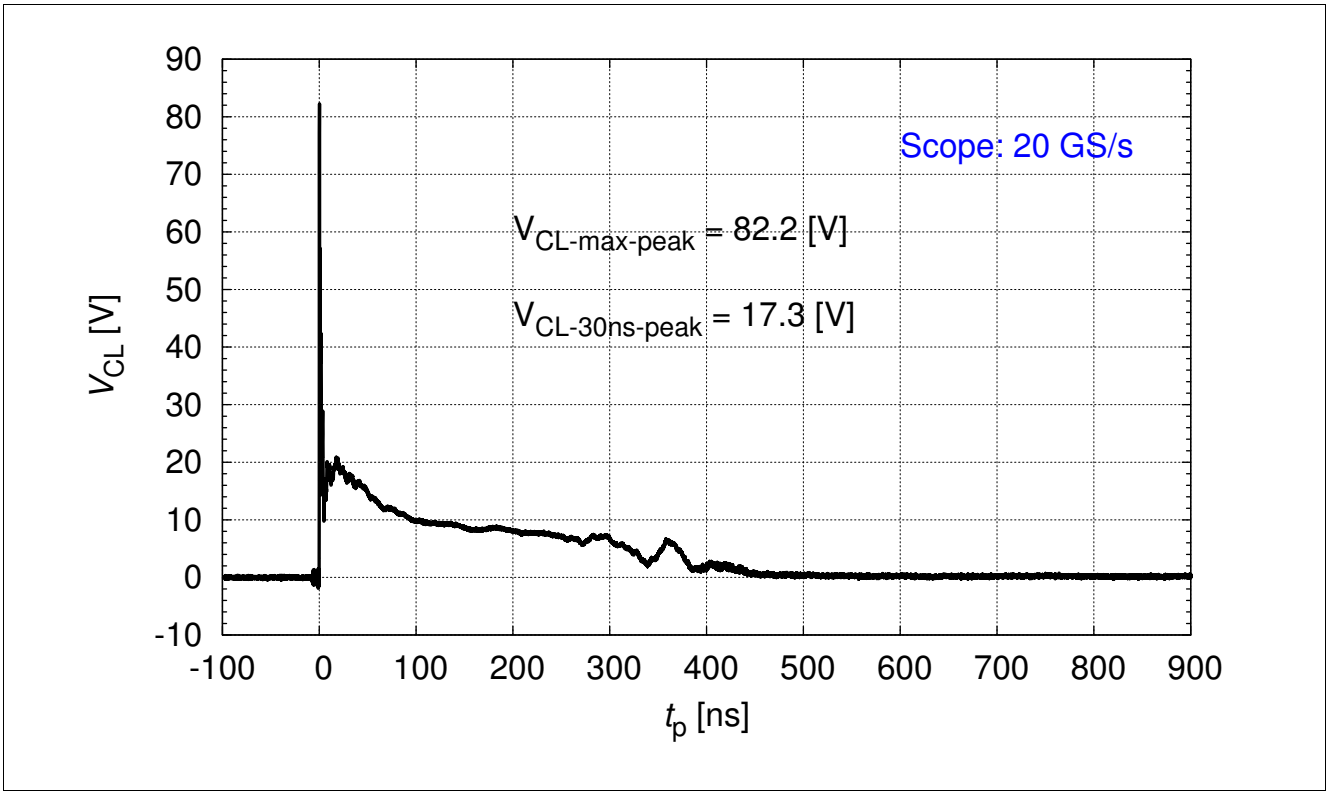



**Figure 3-5 IEC61000-4-2: $V_{CL} = f(t)$, 8 kV positive pulse from pin 1 to pin 2 ($R$ = 330 Ω, $C$ = 150 pF)**

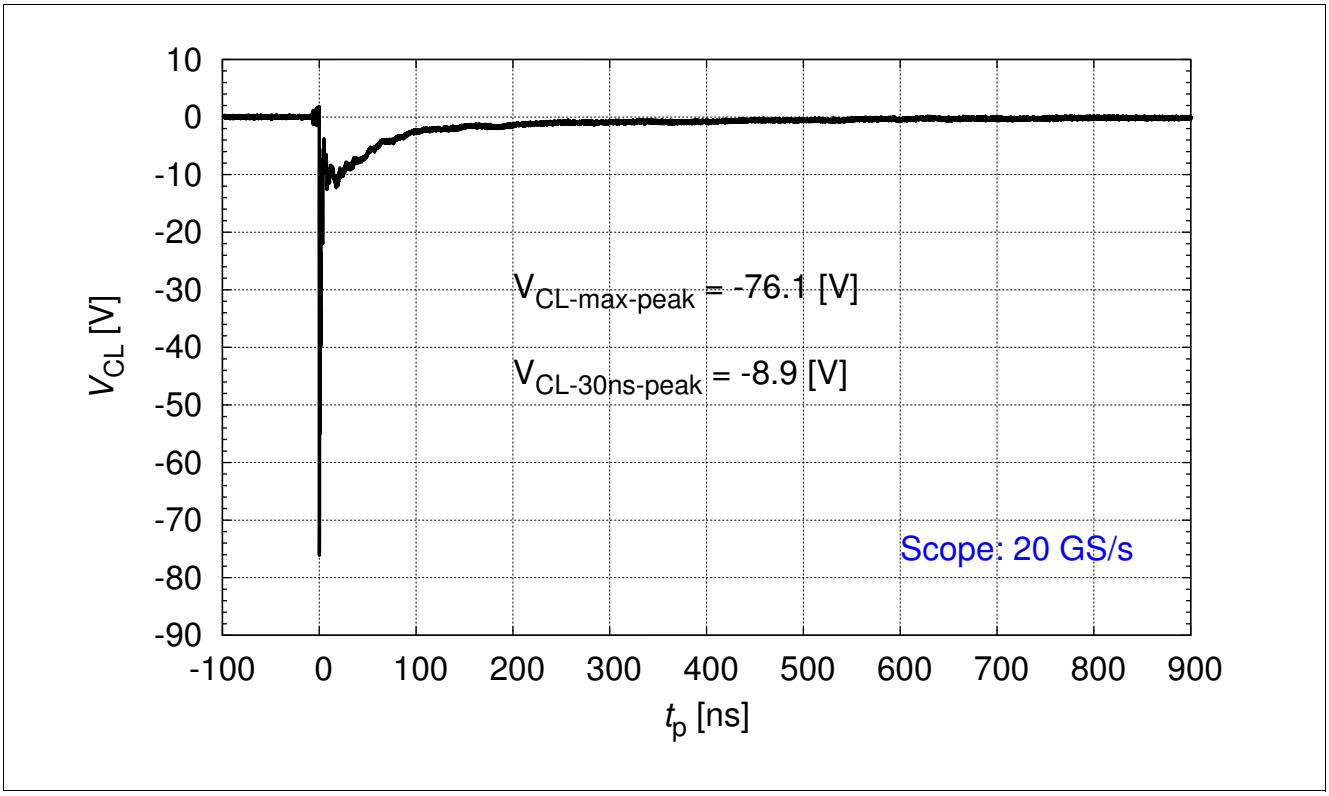



**Figure 3-6 IEC61000-4-2: $V_{CL} = f(t)$, 8 kV negative pulse from pin 1 to pin 2 ($R$ = 330 Ω, $C$ = 150 pF)**

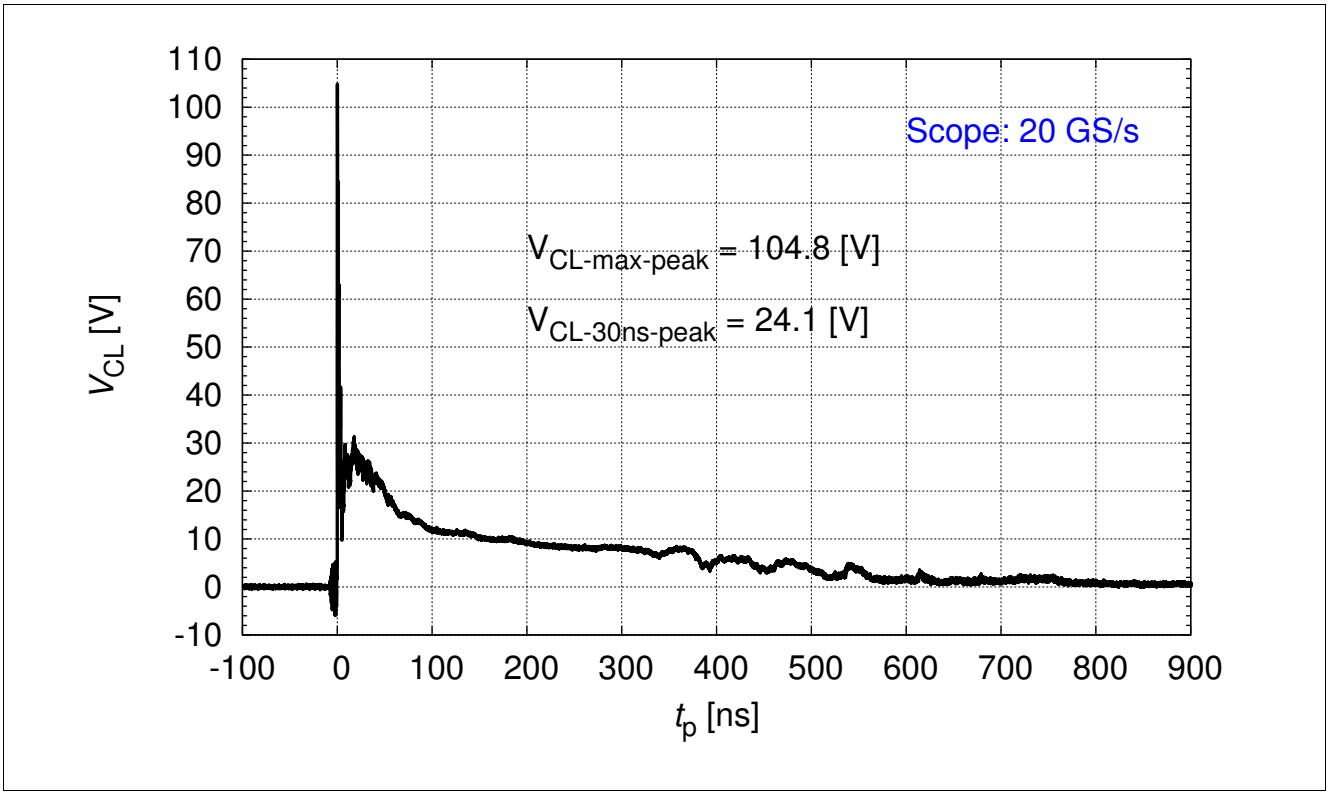



**Figure 3-7 IEC61000-4-2: $V_{CL} = f(t)$, 15 kV positive pulse from pin 1 to pin 2 ($R$ = 330 Ω, $C$ = 150 pF)**

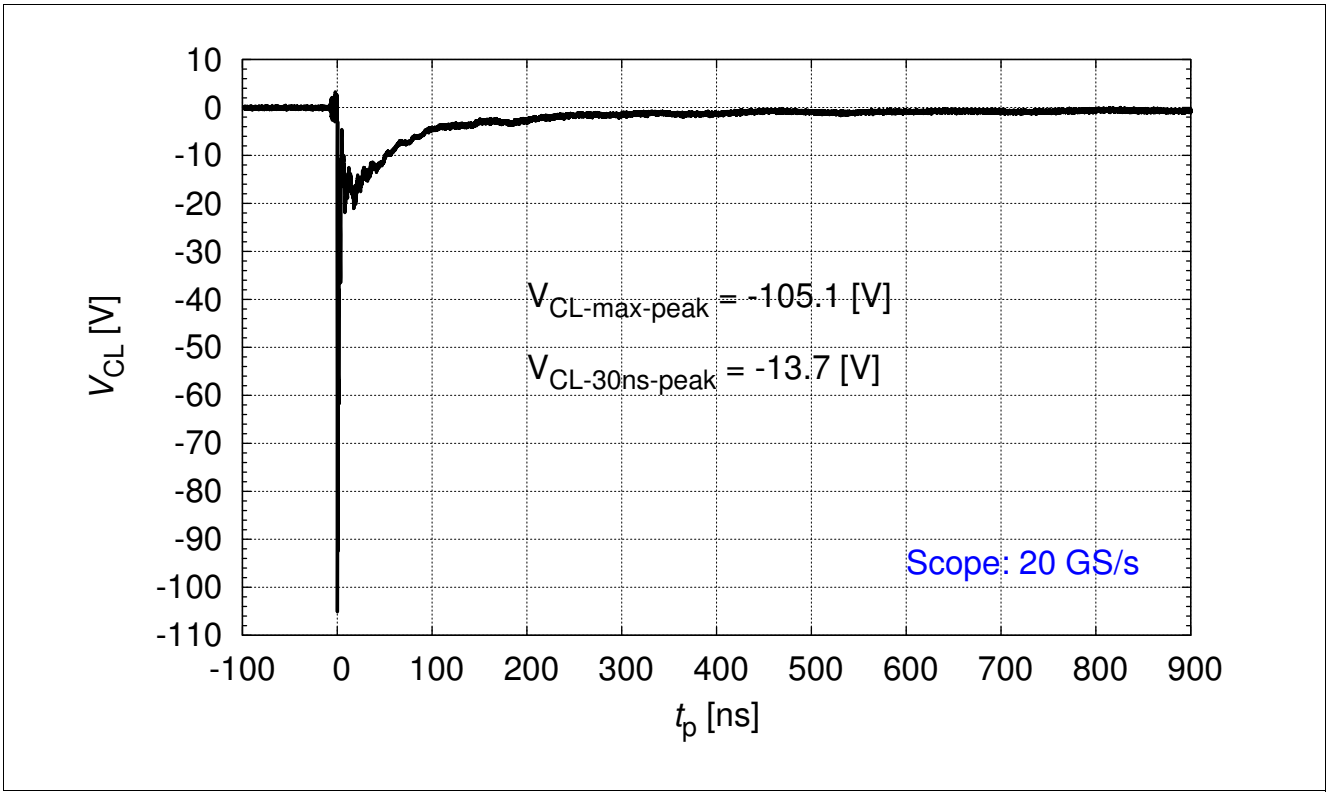



**Figure 3-8 IEC61000-4-2: $V_{CL} = f(t)$, 15 kV negative pulse from pin 1 to pin 2 ($R$ = 330 Ω, $C$ = 150 pF)**

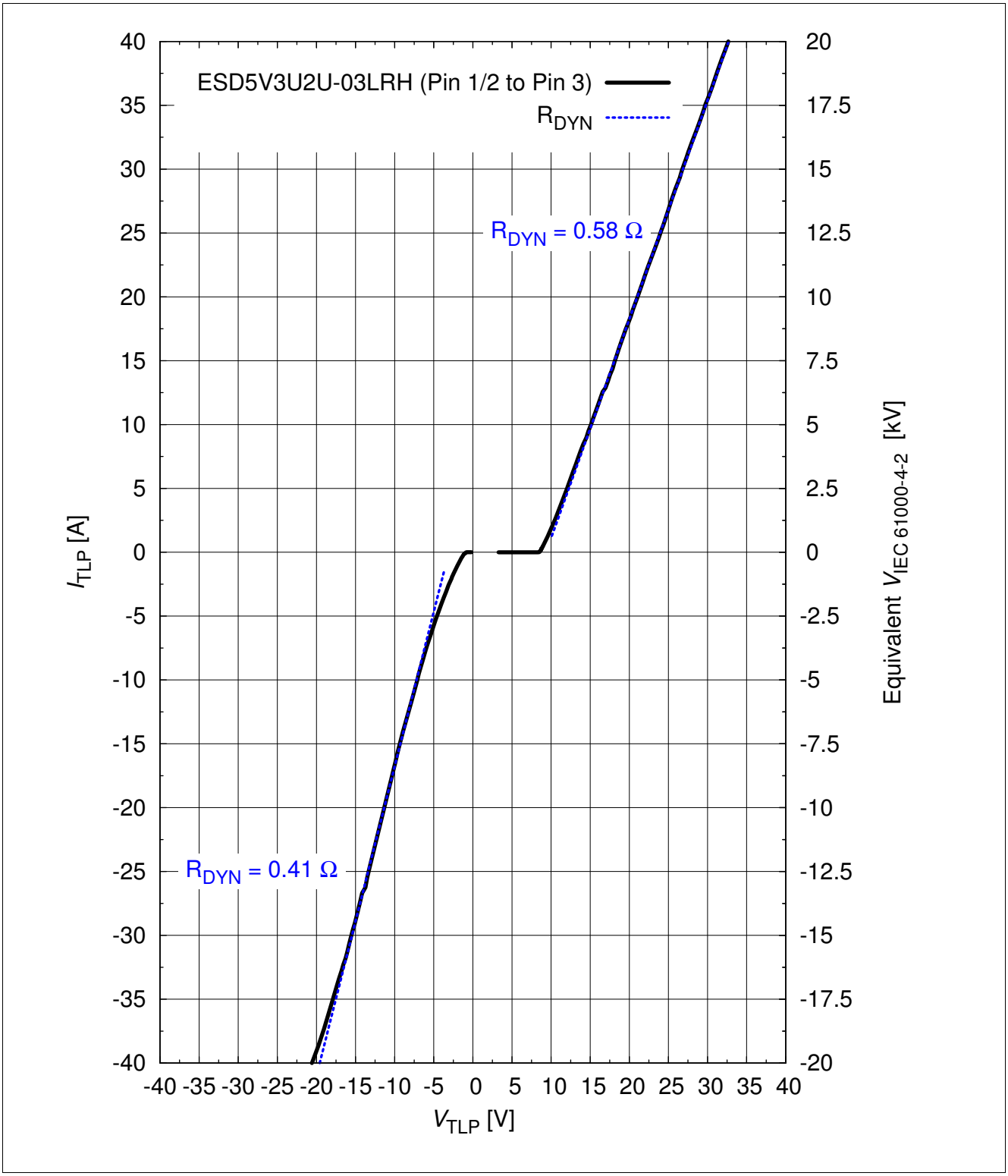



**Figure 3-9 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$ according ANSI/ESD STM5.5.1- Electrostatic Dischange Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: $Z_0$ = 50 Ω, $t_p$ = 100 ns, $t_r$ = 0.6 ns, $I_{TLP}$ and $V_{TLP}$ averaging window: $t_1$ = 30 ns to $t_2$ = 60 ns, extraction of dynamic resistance using squares fit to ELP characterisitic between $I_{TLP1}$ = 10 A and $I_{TLP2}$ = 30 A. Please refer to Application Note AN210 [1]**

# 4 Application Information

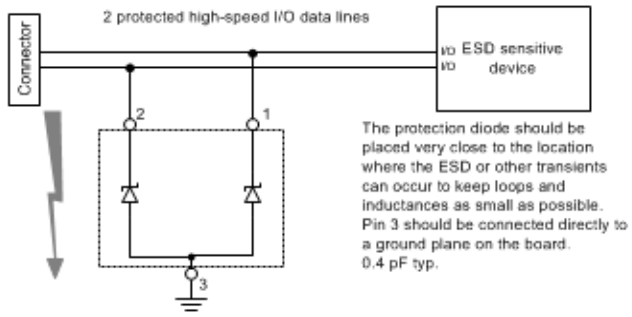



**Figure 4-1 2 lines, uni-directional TVS protection**

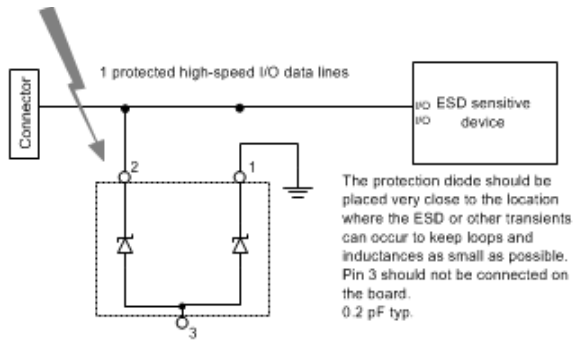



**Figure 4-2 1 line, bi-directional TVS protection**

# 5 Ordering information scheme (examples)

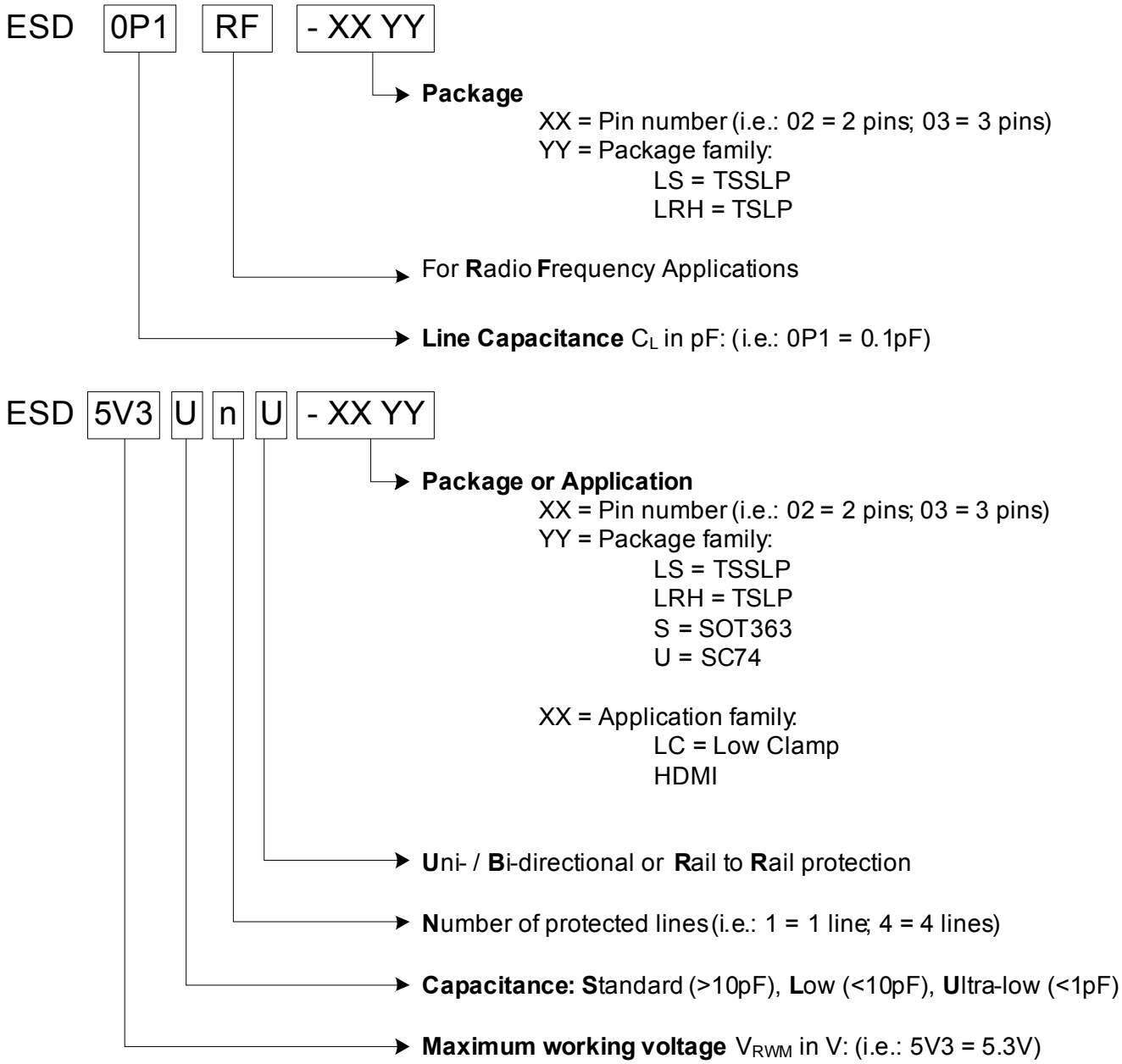



**Figure 5-1 Ordering Information Scheme**

# 6 Package Information

## 6.1 PG-TSFP-3-1

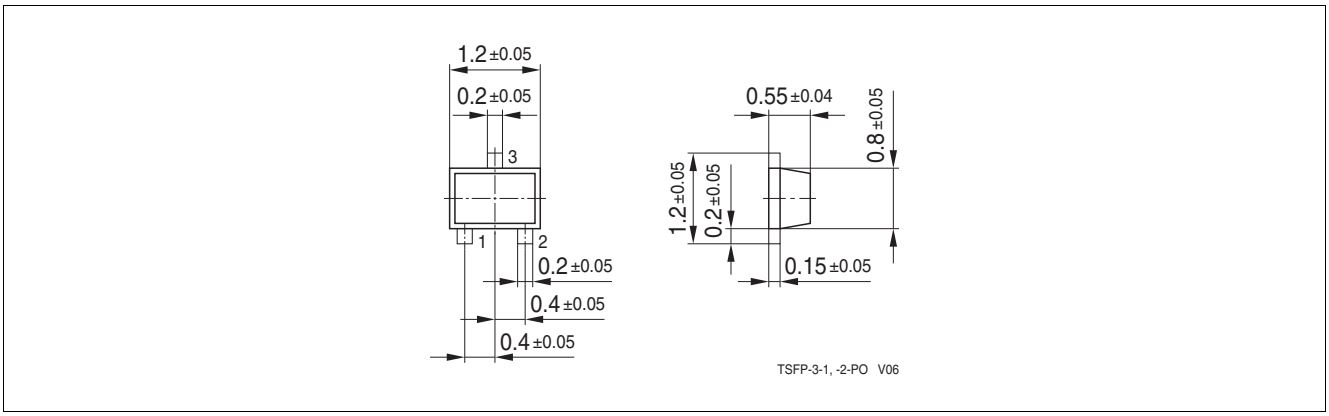



**Figure 6-1 PG-TSFP-3-1: Package Overview**

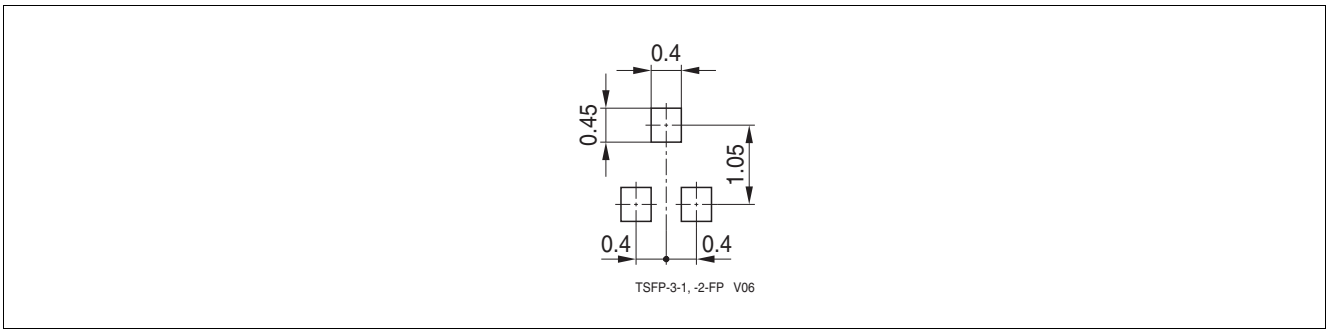



**Figure 6-2 PG-TSFP-3-1: Footprint**

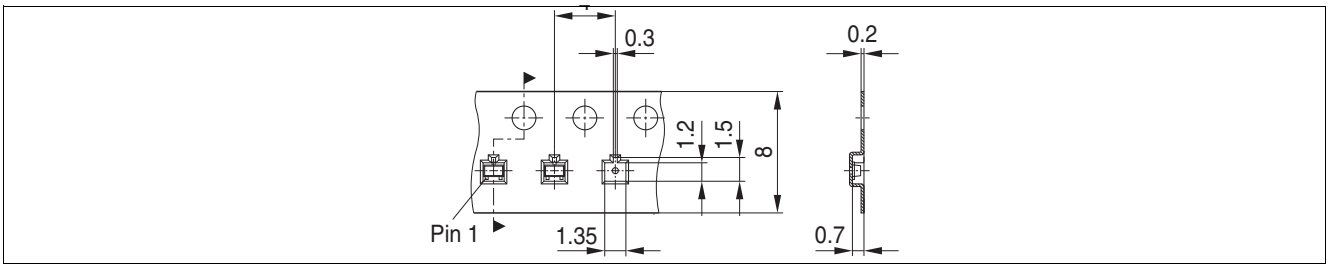



**Figure 6-3 PG-TSFP-3-1: Packing**

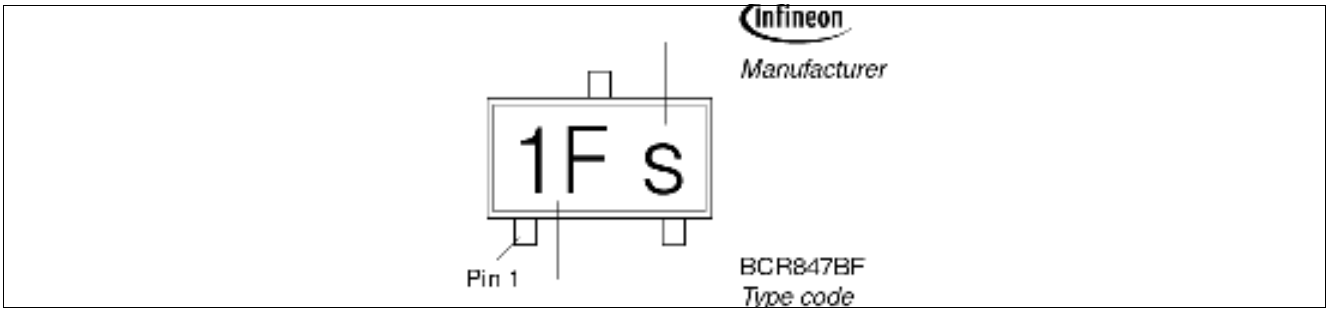



**Figure 6-4 PG-TSFP-3-1: Marking (example)**

## 6.2 PG-TSLP-3-7

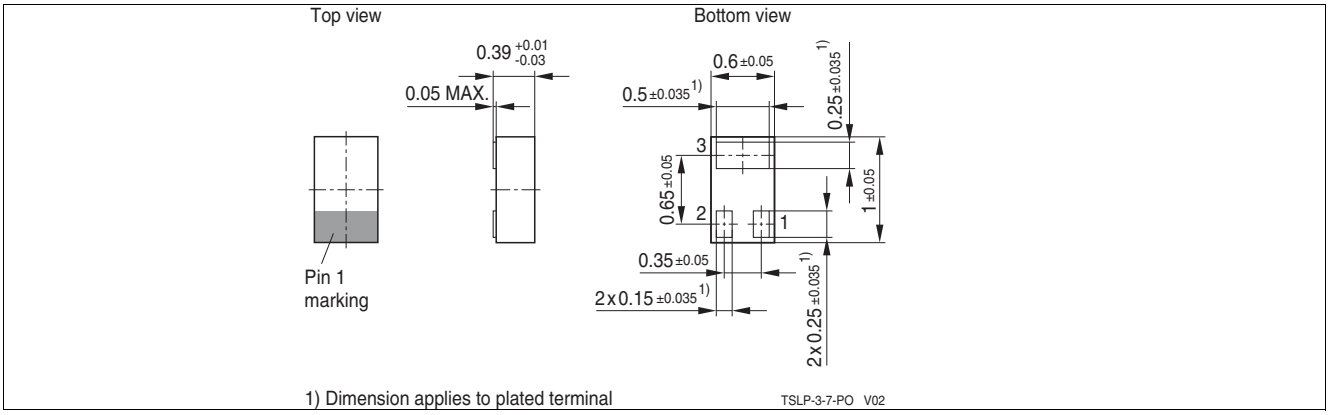



**Figure 6-5 PG-TSLP-3-7: Package Overview**

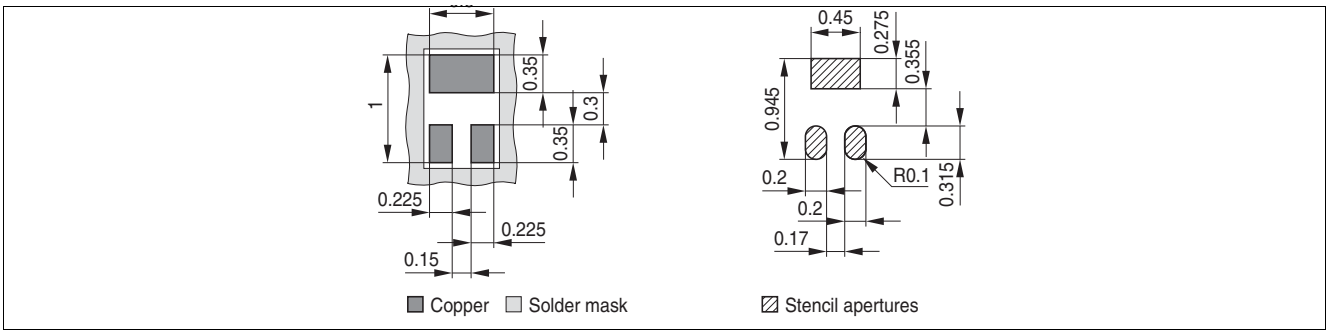



**Figure 6-6 PG-TSLP-3-7: Footprint**

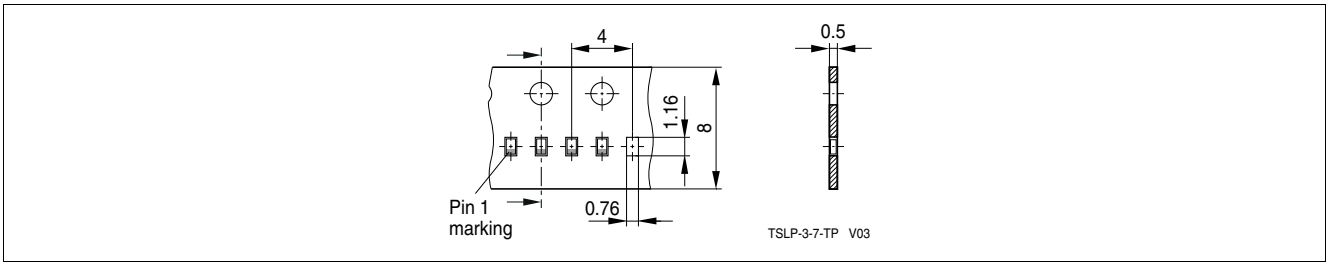



**Figure 6-7 PG-TSLP-3-7: Packing**

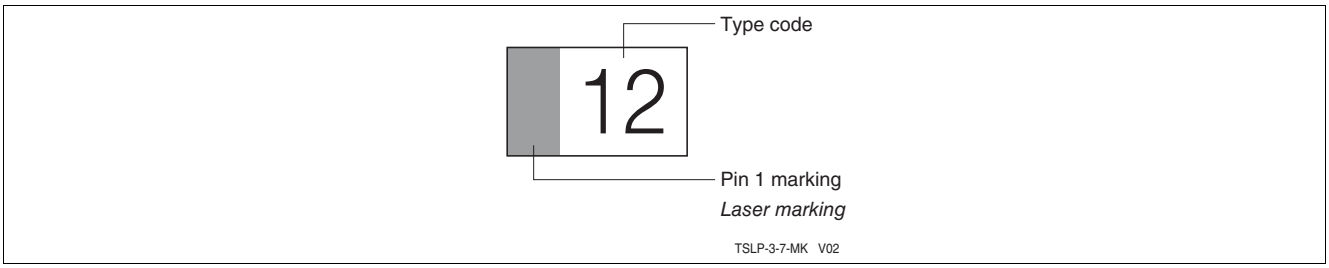



**Figure 6-8 PG-TSLP-3-7: Marking (example)**

# References

[1] Infineon Technologie AG - **Application Note AN210**: Effective ESD Protection Design at System Level Using VF-TLP Characterization Methodology

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